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18. The high voltage resistant edge structure as claimed in claim 16, wherein at least one of said floating guard rings and said inter-ring zones respectively comprise a same width.

19. The high voltage resistant edge structure as claimed in claim 16, wherein a depth of said floating guard rings decreases in a direction of an edge of said semiconductor component.

20. The high voltage resistant edge structure as claimed in claim 16, wherein said floating guard rings have one of a U-shaped or V-shaped cross-section.

21. The high voltage resistant edge structure as claimed in claim 16, further comprising:

at least one space charge zone stopper located at an outermost edge of said edge region of said semiconductor component.

22. The high voltage resistant edge structure as claimed in claim 21, wherein said space charge zone stopper comprises a heavily doped region of said first conductivity type, said heavily doped region being arranged in said inner zone.

23. The high voltage resistant edge structure as claimed in claim 21, wherein said space charge zone stopper comprises a damage implanted region being arranged in said inner zone.

24. The high voltage resistant edge structure edge as claimed in claim 21, wherein said space charge zone stopper comprises an electrode connected to said inner zone, said electrode being one of metallic or containing polysilicon.

25. The high voltage resistant edge structure as claimed in claim 16, further comprising:  
at least one magnetoresistor located at an inner edge of said edge region of said semiconductor component.

26. The high voltage resistant edge structure as claimed in claim 25, wherein at least one of said magnetoresistors is simultaneously a gate electrode of said semiconductor component.

27. The high voltage resistant edge structure as claimed in claim 25, wherein at least an outermost of said magnetoresistors is nearly completely enclosed by a cathode metallization in a direction of said first surface of said semiconductor component.

28. The high voltage resistant edge structure as claimed in claim 27, wherein said cathode metallization is a metallization of a source electrode of said semiconductor component.

29. The high voltage resistant edge structure as claimed in claim 16, wherein said inter-ring zones in said edge region have a cross-section tapered to said first surface.

30. The high voltage resistant edge structure as claimed in claim 16, wherein said semiconductor component is one of a vertical power transistor or an IGBT.

**IN THE ABSTRACT:**

On page 19, cancel lines 1-3, insert the following centered heading at line

1:

**--ABSTRACT OF THE DISCLOSURE--;**

in line 5, cancel "The invention relates to a" substitute --A-- therefor;

in line 6, cancel "the" substitute --a-- therefor;

in line 7, after "of" cancel "the" substitute --a-- therefor;

cancel line